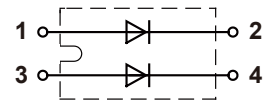
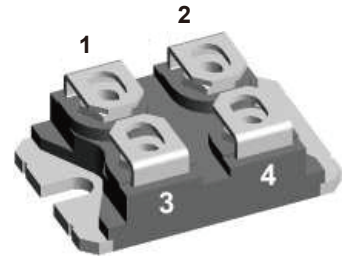


Features

- International standard package
- Isolation voltage 2500 VAC
- 2 independent FRED in 1 package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM}-values
- Soft recovery behaviour

Typical Applications

- Antiparallel diode for high frequency switching devices
- Free wheeling diode in converters and motor control circuits
- Inductive heating and melting
- Ultrasonic cleaners and welders
- Uninterruptible power supplies (UPS)
- Anti saturation diode
- Snubber diode
- AC/DC Motor drives
- Rectifiers in switch mode power supplies (SMPS)



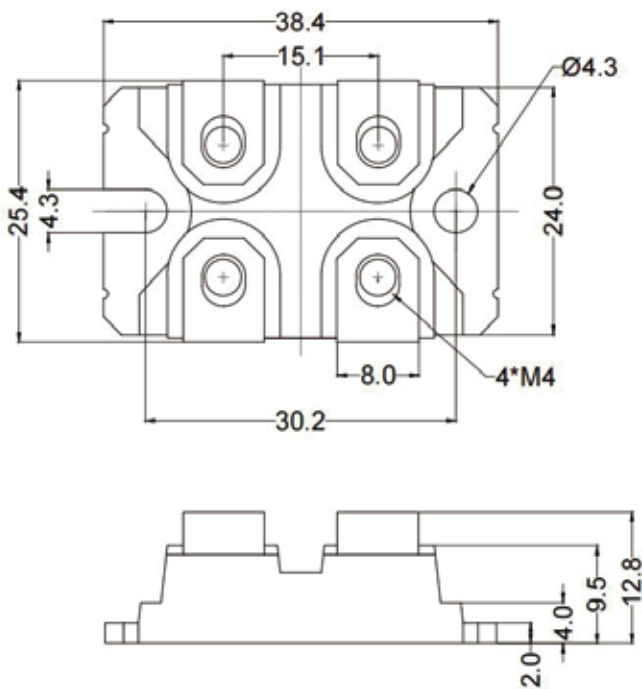
Absolute Maximum Ratings (T_c=25°C Unless Otherwise Specified)

Symbol	Parameter / Test Conditions		Values	Unit
V _R	Maximum d.c. Reverse Voltage		1200	V
V _{RRM}	Maximum Repetitive Reverse Voltage		1200	V
I _{F(AV)}	Average Forward Current	T _c =90°C, Per Diode	125	A
		T _c =90°C, Per Module, T _{vj} =150°C	2x125	A
I _{F(RMS)}	RMS Forward Current	T _c =90°C, Per Diode	196	A
I _{FSM}	Non Repetitive Surge Forward Current	T _j =45°C, 10ms, Sine, peak value	925	A
I ² t	For Fusing	T _j =45°C, 10ms, Sine, peak value	4280	A ² S
		T _j =45°C, 18.3ms, Sine, peak value	4560	A ² S
P _D	Power Dissipation		337	W
T _j	Junction Temperature		-40 to +150	°C
T _{STG}	Storage Temperature Range		-40 to +150	°C
V _{iso}	Isolation Breakdown Voltage	AC , 50Hz(RMS), t=1min	2500	V
R _{thjc}	Junction to Case Thermal Resistance(Per Diode)		0.51	°C/W
Torque	Module to Sink	M4	1.0-1.5	Nm
	Module Electrodes	M4	1.0-1.5	Nm
Weight			30	g

Electrical Characteristics (Tc=25°C Unless Otherwise Specified)

Symbol	Parameter / Test Conditions		Min.	Typ.	Max.	Unit
IRRM	Maximum Reverse Leakage Current	VR=1200V			0.01	mA
		VR=1200V,TJ=150°C			5	mA
VF	Forward Voltage	IF=60A		1.8	2.3	V
		IF=60A,TJ=125°C		1.6		V
trr	Reverse Recovery Time (IF=1A, dIF/dt=-200A/μs,VR=30V)			60		ns
IRM	Maximum Reverse Recovery Current	VR=600V,IF=30A -dIF/dt=200A/μs,Tvj=125°C		15		A

Outlines



miniBLOC, SOT-227